



# LL4148

## SWITCHING DIODE

REVERSE VOLTAGE:75 VOLTS

CURRENT:0.15 AMPERES

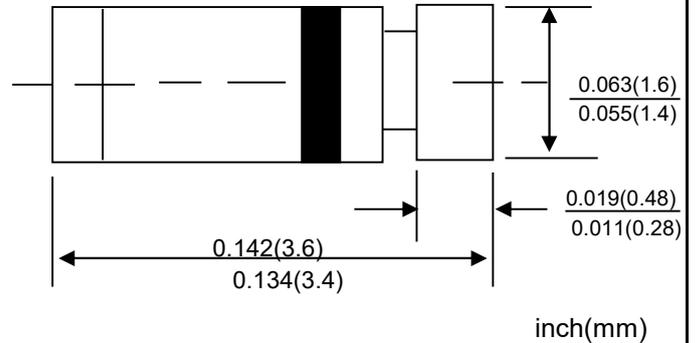
### FEATURES

- Silicon epitaxial planar diode
- High speed switching diode
- 500mV power dissipation
- These diodes are also available in glass case  
Mini-MELF,SOD-323,SOT-323

### MECHANICAL DATA

Case:DO-35,Glass Case  
Polarity: Color band denotes cathode  
Weight: 0.029 gram

### Mini-MELF



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

### MAXIMUN RATINGS

Parameters	Symbols	Value	UNITS
Reverse Voltage	$V_R$	75	V
Peak Reverse Voltage	$V_{RM}$	100	V
Average Forward Rectified Current Half Wave Rectification with Resistive Load at $T_{amb}=25\text{ }^\circ\text{C}$ and $f \geq 50\text{HZ}$	$I_o$	150	mA
Forward Surge Current	$I_{FSM}$	500	mA
Power Dissipation	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_J$	175	°C
Storage Temperature Range	$T_{sTG}$	-65---+175	°C

### ELECTRICAL CHARACTERISTICS

Parameters	Symbol	MIN	MAX	UNITS
Forward Voltage at $I_F=100\text{mA}$	$V_F$		1	V
Leakage Current at $V_R=20\text{V}$	$I_R$		25	nA
at $V_R=75\text{V}$	$I_R$		5	μA
at $V_R=20\text{V } T_J=150^\circ\text{C}$	$I_R$		50	μA
Voltage Rise when Switching ON Tested with 50mA pulses $t_p=0.1\mu\text{s}$ . Rise Time < 30ns. $f_p=5$ to 100HZ	$V_{fr}$		2.5	V
Capacitance at $V_F=V_R=0\text{V}, f=1\text{MHZ}$	$C_{tot}$		4	pF
Reverse Recovery Time= $I_F=10\text{mA}, V_R=6\text{V}, I_R=1\text{mA}, R_L=100\Omega$	$t_{rr}$		4	ns
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		350 <sup>1)</sup>	K/W
Rectification Efficiency at 100MHZ, $V_{FR}=2\text{V}$	nV	0.45		

1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



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